

**PC100 Unbuffered DIMM(168pin)
SPD Specification(256Mb B-die base)**

*Rev. 0.1
Apr. 2000*

SERIAL PRESENCE DETECT

PC100 Unbuffered DIMM

M366S3253BT0-C1H/C1L

- Organization : 32Mx64
- Composition : 32Mx8 * 8
- Used component part # : K4S560832B-TC1H/TC1L
- # of rows in module : 1 Row
- # of banks in component : 4 banks
- Feature : 1,375mil height & single sided component
- Refresh : 8K / 64ms
- Contents ;

Byte #	Function Described	Function		Hex value		Note
		-1H	-1L	-1H	-1L	
0	# of bytes written into serial memory at module manufacturer	128bytes		80h		
1	Total # of bytes of SPD memory device	256bytes (2K-		08h		
2	Fundamental memory type	SDRAM		04h		
3	# of row address on this assembly	13		0Dh		1
4	# of column address on this assembly	10		0Ah		1
5	# of module Rows on this assembly	1 Row		01h		
6	Data width of this assembly	64 bits		40h		
7 Data width of this assembly	-		00h		
8	Voltage interface standard of this assembly	LVTTTL		01h		
9	SDRAM cycle time @CAS latency of 3	10ns	10ns	A0h	A0h	2
10	SDRAM access time from clock @CAS latency of 3	6ns	6ns	60h	60h	2
11	DIMM configuration type	Non parity		00h		
12	Refresh rate & type	7.8us, support		82h		
13	Primary SDRAM width	x8		08h		
14	Error checking SDRAM width	None		00h		
15	Minimum clock delay for back-to-back random column address	tCCD = 1CLK		01h		
16	SDRAM device attributes : Burst lengths supported	1, 2, 4, 8 & full		8Fh		
17	SDRAM device attributes : # of banks on SDRAM device	4 banks		04h		
18	SDRAM device attributes : CAS latency	2 & 3		06h		
19	SDRAM device attributes : CS latency	0 CLK		01h		
20	SDRAM device attributes : Write latency	0 CLK		01h		
21	SDRAM module attributes	Non-buffered, non-registered		00h		
22	SDRAM device attributes : General	+/- 10% volt- age tolerance, Burst Read		0Eh		
23	SDRAM cycle time @CAS latency of 2	10ns	12ns	A0h	C0h	2
24	SDRAM access time from clock @CAS latency of 2	6ns	7ns	60h	70h	2
25	SDRAM cycle time @CAS latency of 1	-	-	00h	00h	
26	SDRAM access time from clock @CAS latency of 1	-	-	00h	00h	
27	Minimum row precharge time (=tRP)	20ns	20ns	14h	14h	
28	Minimum row active to row active delay (tRRD)	20ns	20ns	14h	14h	
29	Minimum RAS to CAS delay (=tRCD)	20ns	20ns	14h	14h	
30	Minimum activate precharge time (=tRAS)	50ns	50ns	32h	32h	
31	Module Row density	1 Row of		40h		
32	Command and address signal input setup time	2ns	2ns	20h	20h	
33	Command and address signal input hold time	1ns	1ns	10h	10h	
34	Data signal input setup time	2ns	2ns	20h	20h	

SERIAL PRESENCE DETECT

PC100 Unbuffered DIMM

Byte #	Function Described	Function Supported		Hex value		Note
		-1H	-1L	-1H	-1L	
35	Data signal input hold time	1ns	1ns	10h	10h	
36~61	Superset information (maybe used in future)	-		00h		
62	SPD data revision code	PC100 SPD Spec. Ver. 1.2A		12h		
63	Checksum for bytes 0 ~ 62	-		39h	69h	
64	Manufacturer JEDEC ID code	Samsung		CEh		
65~71 Manufacturer JEDEC ID code	Samsung		00h		
72	Manufacturing location	Onyang Korea		01h		
73	Manufacturer part # (Memory module)	M		4Dh		
74	Manufacturer part # (DIMM configuration)	3		33h		
75	Manufacturer part # (Data bits)	Blank		20h		
76 Manufacturer part # (Data bits)	6		36h		
77 Manufacturer part # (Data bits)	6		36h		
78	Manufacturer part # (Mode & operating voltage)	S		53h		
79	Manufacturer part # (Module depth)	3		33h		
80 Manufacturer part # (Module depth)	2		32h		
81	Manufacturer part # (Refresh, # of banks in Comp. & interface)	5		35h		
82	Manufacturer part # (Composition component)	3		33h		
83	Manufacturer part # (Component revision)	B		42h		
84	Manufacturer part # (Package type)	T		54h		
85	Manufacturer part # (PCB revision & type)	0		30h		
86	Manufacturer part # (Hyphen)	" - "		2Dh		
87	Manufacturer part # (Power)	C		43h		
88	Manufacturer part # (Minimum cycle time)	1	1	31h	31h	
89	Manufacturer part # (Minimum cycle time)	H	L	48h	4Ch	
90	Manufacturer part # (TBD)	Blank		20h		
91	Manufacturer revision code (For PCB)	0		30h		
92 Manufacturer revision code (For component)	B-die (3rd Gen.)		42h		
93	Manufacturing date (Week)	-		-		3
94	Manufacturing date (Year)	-		-		3
95~98	Assembly serial #	-		-		4
99~125	Manufacturer specific data (may be used in future)	Undefined		-		5
126	System frequency for 100MHz	100MHz		64h		
127	PC100 specification details	Detailed 100MHz Information		AFh	ADh	
128+	Unused storage locations	Undefined		-		5

- Note :**
1. The bank select address is excluded in counting the total # of addresses.
 2. This value is based on the component specification.
 3. These bytes are programmed by code of Date Week & Date Year with BCD format.
 4. These bytes are programmed by Samsung's own Assembly Serial # system. All modules may have different unique serial #.
 5. These bytes are Undefined and can be used for Samsung's own purpose.

SERIAL PRESENCE DETECT

PC100 Unbuffered DIMM

M366S6453BT0-C1H/C1L

- Organization : 64Mx64
- Composition : 32Mx8 *16
- Used component part # : K4S560832B-TC1H/TC1L
- # of rows in module : 2 Rows
- # of banks in component : 4 banks
- Feature : 1,375mil height & double sided component
- Refresh : 8K / 64ms
- **Contents ;**

Byte #	Function Described	Function Supported		Hex value		Note
		-1H	-1L	-1H	-1L	
0	# of bytes written into serial memory at module manufacturer	128bytes		80h		
1	Total # of bytes of SPD memory device	256bytes (2K-bit)		08h		
2	Fundamental memory type	SDRAM		04h		
3	# of row address on this assembly	13		0Dh		1
4	# of column address on this assembly	10		0Ah		1
5	# of module Rows on this assembly	2 Rows		02h		
6	Data width of this assembly	64 bits		40h		
7 Data width of this assembly	-		00h		
8	Voltage interface standard of this assembly	LVTTL		01h		
9	SDRAM cycle time @CAS latency of 3	10ns	10ns	A0h	A0h	2
10	SDRAM access time from clock @CAS latency of 3	6ns	6ns	60h	60h	2
11	DIMM configuration type	Non parity		00h		
12	Refresh rate & type	7.8us, support self refresh		82h		
13	Primary SDRAM width	x8		08h		
14	Error checking SDRAM width	None		00h		
15	Minimum clock delay for back-to-back random column address	tCCD = 1CLK		01h		
16	SDRAM device attributes : Burst lengths supported	1, 2, 4, 8 & full page		8Fh		
17	SDRAM device attributes : # of banks on SDRAM device	4 banks		04h		
18	SDRAM device attributes : CAS latency	2 & 3		06h		
19	SDRAM device attributes : CS latency	0 CLK		01h		
20	SDRAM device attributes : Write latency	0 CLK		01h		
21	SDRAM module attributes	Non-buffered, non-registered & redundant addressing		00h		
22	SDRAM device attributes : General	+/- 10% voltage tolerance, Burst Read Single bit Write precharge all, auto precharge		0Eh		
23	SDRAM cycle time @CAS latency of 2	10ns	12ns	A0h	C0h	2
24	SDRAM access time from clock@CAS latency of 2	6ns	7ns	60h	70h	2
25	SDRAM cycle time @CAS latency of 1	-	-	00h	00h	
26	SDRAM access time from clock@CAS latency of 1	-	-	00h	00h	
27	Minimum row precharge time (=tRP)	20ns	20ns	14h	14h	
28	Minimum row active to row active delay (tRRD)	20ns	20ns	14h	14h	
29	Minimum RAS to CAS delay (=tRCD)	20ns	20ns	14h	14h	
30	Minimum activate precharge time (=tRAS)	50ns	50ns	32h	32h	
31	Module Row density	2 Rows of 256MB		40h		
32	Command and address signal input setup time	2ns	2ns	20h	20h	
33	Command and address signal input hold time	1ns	1ns	10h	10h	
34	Data signal input setup time	2ns	2ns	20h	20h	

SERIAL PRESENCE DETECT

PC100 Unbuffered DIMM

Byte #	Function Described	Function Supported		Hex value		Note
		-1H	-1L	-1H	-1L	
35	Data signal input hold time	1ns	1ns	10h	10h	
36~61	Superset information (maybe used in future)	-		00h		
62	SPD data revision code	PC100 SPD Spec. Ver. 1.2A		12h		
63	Checksum for bytes 0 ~ 62	-		3Ah	6Ah	
64	Manufacturer JEDEC ID code	Samsung		CEh		
65~71 Manufacturer JEDEC ID code	Samsung		00h		
72	Manufacturing location	Onyang Korea		01h		
73	Manufacturer part # (Memory module)	M		4Dh		
74	Manufacturer part # (DIMM configuration)	3		33h		
75	Manufacturer part # (Data bits)	Blank		20h		
76 Manufacturer part # (Data bits)	6		36h		
77 Manufacturer part # (Data bits)	6		36h		
78	Manufacturer part # (Mode & operating voltage)	S		53h		
79	Manufacturer part # (Module depth)	6		36h		
80 Manufacturer part # (Module depth)	4		34h		
81	Manufacturer part # (Refresh, # of banks in Comp. & interface)	5		35h		
82	Manufacturer part # (Composition component)	3		33h		
83	Manufacturer part # (Component revision)	B		42h		
84	Manufacturer part # (Package type)	T		54h		
85	Manufacturer part # (PCB revision & type)	0		30h		
86	Manufacturer part # (Hyphen)	" - "		2Dh		
87	Manufacturer part # (Power)	C		43h		
88	Manufacturer part # (Minimum cycle time)	1	1	31h	31h	
89	Manufacturer part # (Minimum cycle time)	H	L	48h	4Ch	
90	Manufacturer part # (TBD)	Blank		20h		
91	Manufacturer revision code (For PCB)	0		30h		
92 Manufacturer revision code (For component)	B-die (3rd Gen.)		42h		
93	Manufacturing date (Week)	-		-		3
94	Manufacturing date (Year)	-		-		3
95~98	Assembly serial #	-		-		4
99~125	Manufacturer specific data (may be used in future)	Undefined		-		5
126	System frequency for 100MHz	100MHz		64h		
127	PC100 specification details	Detailed 100MHz Information		FFh	FDh	
128+	Unused storage locations	Undefined		-		5

- Note :**
1. The bank select address is excluded in counting the total # of addresses.
 2. This value is based on the component specification.
 3. These bytes are programmed by code of Date Week & Date Year with BCD format.
 4. These bytes are programmed by Samsung's own Assembly Serial # system. All modules may have different unique serial #.
 5. These bytes are Undefined and can be used for Samsung's own purpose.

SERIAL PRESENCE DETECT

PC100 Unbuffered DIMM

M374S3253BT0-C1H/C1L

- Organization : 32Mx72
- Composition : 32Mx8 *9
- Used component part # : K4S560832B-TC1H/TC1L
- # of rows in module : 1 Row
- # of banks in component : 4 banks
- Feature : 1,375mil height & single sided component
- Refresh : 8K / 64ms
- Contents ;

Byte #	Function Described	Function Supported		Hex value		Note
		-1H	-1L	-1H	-1L	
0	# of bytes written into serial memory at module manufacturer	128bytes		80h		
1	Total # of bytes of SPD memory device	256bytes (2K-bit)		08h		
2	Fundamental memory type	SDRAM		04h		
3	# of row address on this assembly	13		0Dh		1
4	# of column address on this assembly	10		0Ah		1
5	# of module Rows on this assembly	1 Row		01h		
6	Data width of this assembly	72 bits		48h		
7 Data width of this assembly	-		00h		
8	Voltage interface standard of this assembly	LVTTL		01h		
9	SDRAM cycle time @CAS latency of 3	10ns	10ns	A0h	A0h	2
10	SDRAM access time from clock @CAS latency of 3	6ns	6ns	60h	60h	2
11	DIMM configuration type	ECC		02h		
12	Refresh rate & type	7.8 us, support self refresh		82h		
13	Primary SDRAM width	x8		08h		
14	Error checking SDRAM width	x8		08h		
15	Minimum clock delay for back-to-back random column address	tCCD = 1CLK		01h		
16	SDRAM device attributes : Burst lengths supported	1, 2, 4, 8 & full page		8Fh		
17	SDRAM device attributes : # of banks on SDRAM device	4 banks		04h		
18	SDRAM device attributes : CAS latency	2 & 3		06h		
19	SDRAM device attributes : CS latency	0 CLK		01h		
20	SDRAM device attributes : Write latency	0 CLK		01h		
21	SDRAM module attributes	Non-buffered, non-registered & redundant addressing		00h		
22	SDRAM device attributes : General	+/- 10% voltage tolerance, Burst Read Single bit Write precharge all, auto precharge		0Eh		
23	SDRAM cycle time @CAS latency of 2	10ns	12ns	A0h	C0h	2
24	SDRAM access time from clock @CAS latency of 2	6ns	7ns	60h	70h	2
25	SDRAM cycle time @CAS latency of 1	-	-	00h	00h	
26	SDRAM access time from clock @CAS latency of 1	-	-	00h	00h	
27	Minimum row precharge time (=tRP)	20ns	20ns	14h	14h	
28	Minimum row active to row active delay (tRRD)	20ns	20ns	14h	14h	
29	Minimum RAS to CAS delay (=tRCD)	20ns	20ns	14h	14h	
30	Minimum activate precharge time (=tRAS)	50ns	50ns	32h	32h	
31	Module Row density	1 Row of 256MB		40h		
32	Command and address signal input setup time	2ns	2ns	20h	20h	
33	Command and address signal input hold time	1ns	1ns	10h	10h	
34	Data signal input setup time	2ns	2ns	20h	20h	

SERIAL PRESENCE DETECT

PC100 Unbuffered DIMM

Byte #	Function Described	Function Supported		Hex value		Note
		-1H	-1L	-1H	-1L	
35	Data signal input hold time	1ns	1ns	10h	10h	
36~61	Superset information (maybe used in future)	-		00h		
62	SPD data revision code	PC100 SPD Spec. Ver. 1.2A		12h		
63	Checksum for bytes 0 ~ 62	-		4Bh	7Bh	
64	Manufacturer JEDEC ID code	Samsung		CEh		
65~71 Manufacturer JEDEC ID code	Samsung		00h		
72	Manufacturing location	Onyang Korea		01h		
73	Manufacturer part # (Memory module)	M		4Dh		
74	Manufacturer part # (DIMM configuration)	3		33h		
75	Manufacturer part # (Data bits)	Blank		20h		
76 Manufacturer part # (Data bits)	7		37h		
77 Manufacturer part # (Data bits)	4		34h		
78	Manufacturer part # (Mode & operating voltage)	S		53h		
79	Manufacturer part # (Module depth)	3		33h		
80 Manufacturer part # (Module depth)	2		32h		
81	Manufacturer part # (Refresh, # of banks in Comp. & interface)	5		35h		
82	Manufacturer part # (Composition component)	3		33h		
83	Manufacturer part # (Component revision)	B		42h		
84	Manufacturer part # (Package type)	T		54h		
85	Manufacturer part # (PCB revision & type)	0		30h		
86	Manufacturer part # (Hyphen)	" - "		2Dh		
87	Manufacturer part # (Power)	C		43h		
88	Manufacturer part # (Minimum cycle time)	1	1	31h	31h	
89	Manufacturer part # (Minimum cycle time)	H	L	48h	4Ch	
90	Manufacturer part # (TBD)	Blank		20h		
91	Manufacturer revision code (For PCB)	0		30h		
92 Manufacturer revision code (For component)	B-die (3rd Gen.)		42h		
93	Manufacturing date (Week)	-		-		3
94	Manufacturing date (Year)	-		-		3
95~98	Assembly serial #	-		-		4
99~125	Manufacturer specific data (may be used in future)	Undefined		-		5
126	System frequency for 100MHz	100MHz		64h		
127	PC100 specification details	Detailed 100MHz Information		AFh	ADh	
128+	Unused storage locations	Undefined		-		5

- Note :**
1. The bank select address is excluded in counting the total # of addresses.
 2. This value is based on the component specification.
 3. These bytes are programmed by code of Date Week & Date Year with BCD format.
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SERIAL PRESENCE DETECT

PC100 Unbuffered DIMM

M374S6453BT0-C1H/C1L

- Organization : 64Mx72
- Composition : 32Mx8 *18
- Used component part # : K4S560832B-TC1H/TC1L
- # of rows in module : 2 Rows
- # of banks in component : 4 banks
- Feature : 1,375mil height & double sided component
- Refresh : 8K / 64ms
- **Contents ;**

Byte #	Function Described	Function Supported		Hex value		Note
		-1H	-1L	-1H	-1L	
0	# of bytes written into serial memory at module manufacturer	128bytes		80h		
1	Total # of bytes of SPD memory device	256bytes (2K-bit)		08h		
2	Fundamental memory type	SDRAM		04h		
3	# of row address on this assembly	13		0Dh		1
4	# of column address on this assembly	10		0Ah		1
5	# of module Rows on this assembly	2 Rows		02h		
6	Data width of this assembly	72 bits		48h		
7 Data width of this assembly	-		00h		
8	Voltage interface standard of this assembly	LVTTTL		01h		
9	SDRAM cycle time @CAS latency of 3	10ns	10ns	A0h	A0h	2
10	SDRAM access time from clock @CAS latency of 3	6ns	6ns	60h	60h	2
11	DIMM configuration type	ECC		02h		
12	Refresh rate & type	7.8us, support self refresh		82h		
13	Primary SDRAM width	x8		08h		
14	Error checking SDRAM width	x8		08h		
15	Minimum clock delay for back-to-back random column address	tCCD = 1CLK		01h		
16	SDRAM device attributes : Burst lengths supported	1, 2, 4, 8 & full page		8Fh		
17	SDRAM device attributes : # of banks on SDRAM device	4 banks		04h		
18	SDRAM device attributes : CAS latency	2 & 3		06h		
19	SDRAM device attributes : CS latency	0 CLK		01h		
20	SDRAM device attributes : Write latency	0 CLK		01h		
21	SDRAM module attributes	Non-buffered, non-registered & redundant addressing		00h		
22	SDRAM device attributes : General	+/- 10% voltage tolerance, Burst Read Single bit Write precharge all, auto precharge		0Eh		
23	SDRAM cycle time @CAS latency of 2	10ns	12ns	A0h	C0h	2
24	SDRAM access time from clock @CAS latency of 2	6ns	7ns	60h	70h	2
25	SDRAM cycle time @CAS latency of 1	-	-	00h	00h	
26	SDRAM access time from clock @CAS latency of 1	-	-	00h	00h	
27	Minimum row precharge time (=tRP)	20ns	20ns	14h	14h	
28	Minimum row active to row active delay (tRRD)	20ns	20ns	14h	14h	
29	Minimum RAS to CAS delay (=tRCD)	20ns	20ns	14h	14h	
30	Minimum activate precharge time (=tRAS)	50ns	50ns	32h	32h	
31	Module Row density	2 Rows of 256MB		40h		
32	Command and address signal input setup time	2ns	2ns	20h	20h	
33	Command and address signal input hold time	1ns	1ns	10h	10h	
34	Data signal input setup time	2ns	2ns	20h	20h	

SERIAL PRESENCE DETECT

PC100 Unbuffered DIMM

Byte #	Function Described	Function Supported		Hex value		Note
		-1H	-1L	-1H	-1L	
35	Data signal input hold time	1ns	1ns	10h	10h	
36~61	Superset information (maybe used in future)	-		00h		
62	SPD data revision code	PC100 SPD Spec. Ver. 1.2A		12h		
63	Checksum for bytes 0 ~ 62	-		4Ch	7Ch	
64	Manufacturer JEDEC ID code	Samsung		CEh		
65~71 Manufacturer JEDEC ID code	Samsung		00h		
72	Manufacturing location	Onyang Korea		01h		
73	Manufacturer part # (Memory module)	M		4Dh		
74	Manufacturer part # (DIMM configuration)	3		33h		
75	Manufacturer part # (Data bits)	Blank		20h		
76 Manufacturer part # (Data bits)	7		37h		
77 Manufacturer part # (Data bits)	4		34h		
78	Manufacturer part # (Mode & operating voltage)	S		53h		
79	Manufacturer part # (Module depth)	6		36h		
80 Manufacturer part # (Module depth)	4		34h		
81	Manufacturer part # (Refresh, # of banks in Comp. & interface)	5		35h		
82	Manufacturer part # (Composition component)	3		33h		
83	Manufacturer part # (Component revision)	B		42h		
84	Manufacturer part # (Package type)	T		54h		
85	Manufacturer part # (PCB revision & type)	0		30h		
86	Manufacturer part # (Hyphen)	" - "		2Dh		
87	Manufacturer part # (Power)	C		43h		
88	Manufacturer part # (Minimum cycle time)	1	1	31h	31h	
89	Manufacturer part # (Minimum cycle time)	H	L	48h	4Ch	
90	Manufacturer part # (TBD)	Blank		20h		
91	Manufacturer revision code (For PCB)	0		30h		
92 Manufacturer revision code (For component)	B-die (3rd Gen.)		42h		
93	Manufacturing date (Week)	-		-		3
94	Manufacturing date (Year)	-		-		3
95~98	Assembly serial #	-		-		4
99~125	Manufacturer specific data (may be used in future)	Undefined		-		5
126	System frequency for 100MHz	100MHz		64h		
127	PC100 specification details	Detailed 100MHz Information		FFh	FDh	
128+	Unused storage locations	Undefined		-		5

- Note :**
1. The bank select address is excluded in counting the total # of addresses.
 2. This value is based on the component specification.
 3. These bytes are programmed by code of Date Week & Date Year with BCD format.
 4. These bytes are programmed by Samsung's own Assembly Serial # system. All modules may have different unique serial #.
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